
2SC4367

Silicon NPN Epitaxial

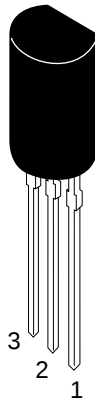
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Application

High Frequency amplifier

Outline

TO-92MOD



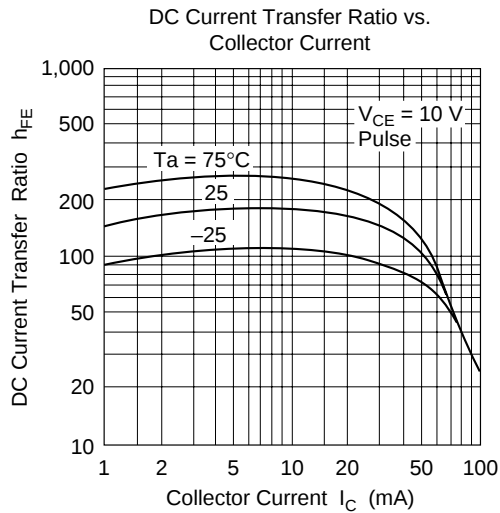
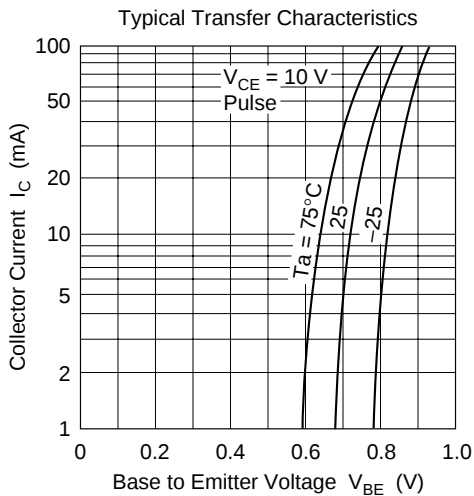
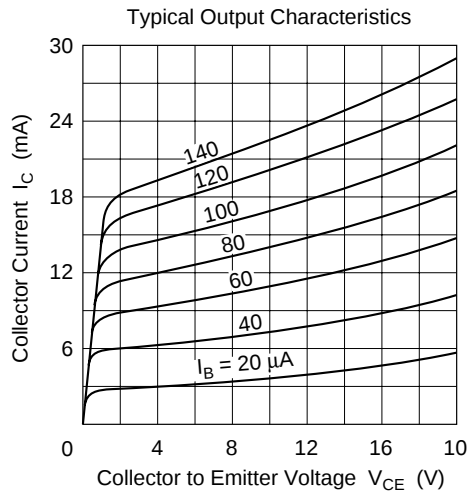
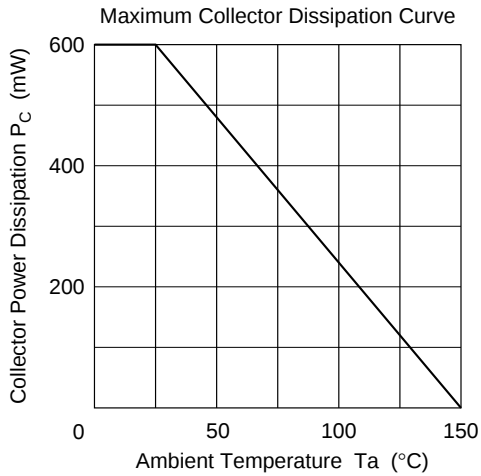
- 1. Emitter
- 2. Collector
- 3. Base

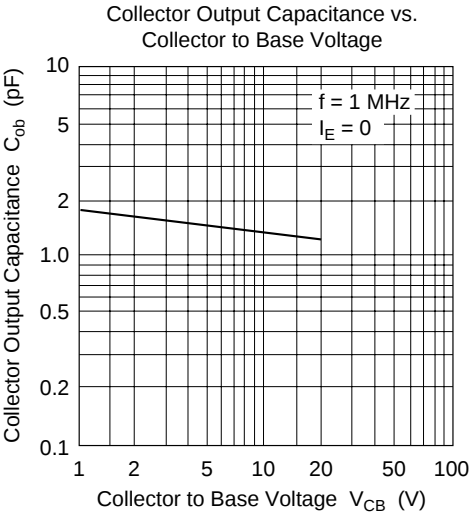
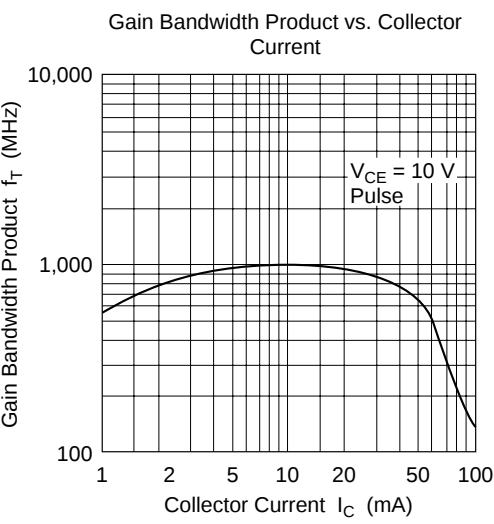
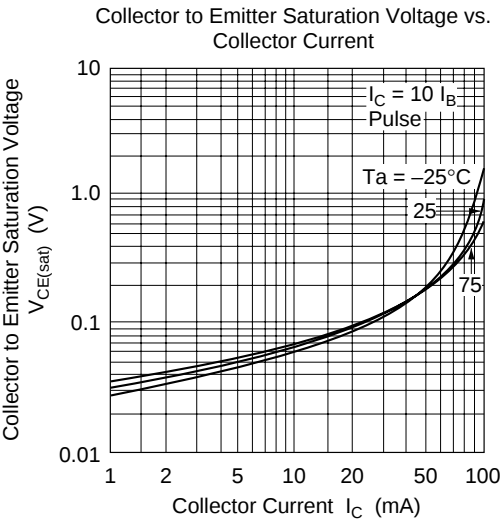
Absolute Maximum Ratings (Ta = 25°C)

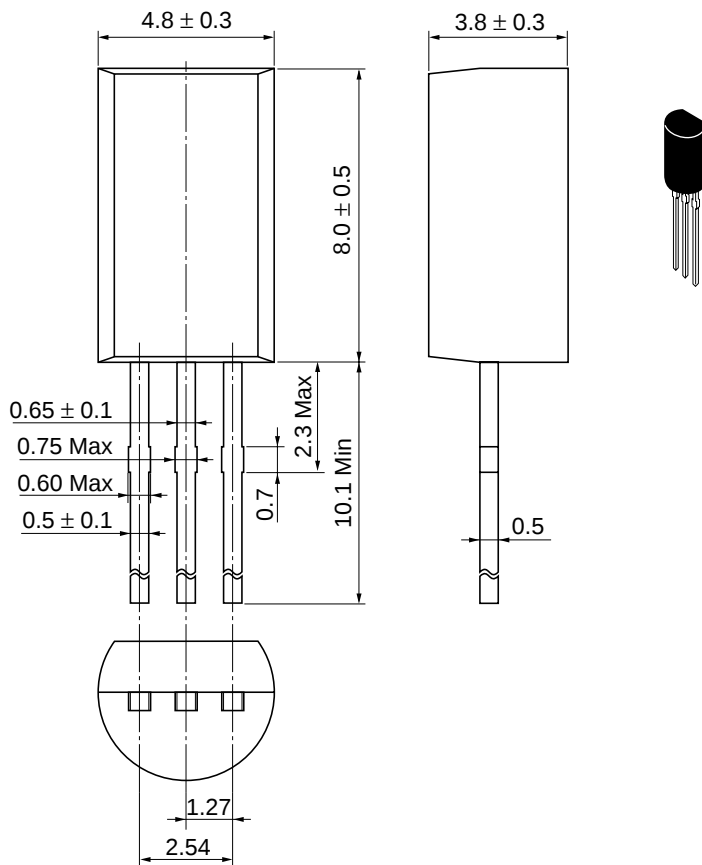
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	100	mA
Collector peak current	$i_{C\ (peak)}$	200	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10\ \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 3\ mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	3	—	—	V	$I_E = 10\ \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1.0	μA	$V_{CB} = 10\ V, I_E = 0$
DC current transfer ratio	h_{FE}	40	—	—		$V_{CE} = 10\ V, I_C = 10\ mA$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 20\ mA, I_B = 4\ mA$
Gain bandwidth product	f_T	600	1000	—	MHz	$V_{CE} = 10\ V, I_C = 10\ mA$
Collector output capacitance	C_{ob}	—	1.3	—	pF	$V_{CB} = 10\ V, I_E = 0, f = 1\ MHz$







Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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